ABSTRACT

The object is to form a resist pattern to be applicable to a thermal flow process with a small changing amount of the resist pattern size per unit temperature, high uniformity within the plane of the resist hole pattern size obtained and an excellent cross sectional profile. In a resist pattern forming method by subjecting a patterned positive-working resist film provided on a substrate to a thermal flow treatment to effect size reduction, it is characterized in (a) that, as the positive-working resist composition to be used, a positive-working resist composition is used which comprises (A) a resinous ingredient capable of being imparted with increased solubility in alkali by an acid, (B) a compound generating an acid by irradiation with a radiation, (C) a compound having at least two vinyl ether groups per molecule to form crosslinks by reacting with the resinous ingredient (A) under heating and (D) an organic amine compound and (b) that the aforementioned thermal flow treatment is conducted by twice or more of heatings within a temperature range of 100-200 °C wherein the temperature of subsequent heating is not lower than the temperature in the preceding heating.



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